TOSHIBA GTR Module Silicon N Channel IGBT

# MG100J2YS50

## High Power Switching Applications Motor Control Applications

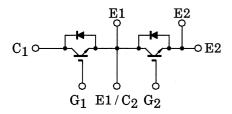
- The electrodes are isolated from case.
- High input impedance.
- Includes a complete half bridge in one package.
- Enhancement-mode.
- High speed:  $t_f = 0.30 \mu s$  (Max) (IC = 100A)

 $t_{rr} = 0.15 \mu s \text{ (Max) (IF} = 100 \text{A)}$ 

Low saturation voltage

: VCE (sat)=2.70V (Max) (IC=100A)

## **Equivalent Circuit**



# Unit: mm 3-M5 E2 4-FAST-ON-TAB #110 23±0.5 23±0.5 B1 23±0.5 23±0.5 B1 3-M5 E2 2-\$5.6±0.3 27±0.5 4±0.5 4±0.5 9.9±0.8 18±0.5 19±0.5 18±0.5 33.3±0.5 JEDEC EIAJ TOSHIBA 2-94D1A

Weight: 202g (Typ.)

## **Maximum Ratings (Ta = 25°C)**

Characteristic		Symbol	Rating	Unit	
Collector-emitter voltage		V <sub>CES</sub>	600	V	
Gate-emitter voltage		V <sub>GES</sub>	±20	V	
Collector current	DC	I <sub>C</sub>	100	Α	
	1ms	I <sub>CP</sub>	200		
Forward current	DC	l <sub>F</sub>	100	А	
	1ms	I <sub>FM</sub>	200		
Collector power dissipation (Tc=25°C)		P <sub>C</sub>	450	W	
Junction temperature		Tj	150	°C	
Storage temperature range		T <sub>stg</sub>	-40 ~ 125	°C	
Isolation voltage		V <sub>Isol</sub>	2500 (AC 1 min.)	V	
Screw torque (Terminal / mounting)		_	3/3	N·m	

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damage to property.

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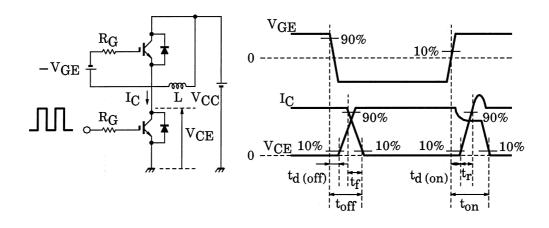


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## **Electrical Characteristics (Ta = 25°C)**

C	characteristic	Symbol	Test Condition	Min	Тур.	Max	Unit	
Gate leakage current		I <sub>GES</sub>	V <sub>GE</sub> = ±20V, V <sub>CE</sub> = 0	_	_	±500	nA	
Collector cut-off current		I <sub>CES</sub>	V <sub>CE</sub> = 600V, V <sub>GE</sub> = 0	_	_	1.0	mA	
Gate-emitter cut-off voltage		V <sub>GE (off)</sub>	I <sub>C</sub> = 10mA, V <sub>CE</sub> = 5V	5.0	7.0	8.0	V	
Collector-emitte	r saturation voltage	V <sub>CE (sat)</sub>	I <sub>C</sub> = 100A, V <sub>GE</sub> = 15V	_	2.10	2.70	V	
Input capacitan	ce	C <sub>ies</sub>	V <sub>CE</sub> = 10V, V <sub>GE</sub> =0, f = 1MHz	_	9000	_	pF	
Switching time	Turn-on delay time	t <sub>d (on)</sub>	Inductive load $V_{CC} = 300V$ $I_{C} = 100A$ $V_{GE} = \pm 15V$ $R_{G} = 13\Omega$ (Note 1)	_	0.08	0.16	- μs	
	Rise time	t <sub>r</sub>		_	0.12	0.24		
	Turn-on time	t <sub>on</sub>		_	0.40	0.80		
	Turn-off delay time	t <sub>d (off)</sub>		_	0.20	0.40		
	Fall time	t <sub>f</sub>		_	0.15	0.30		
	Turn-off time	t <sub>off</sub>		_	0.50	1.00		
Forward voltage	)	٧F	I <sub>F</sub> = 100A, V <sub>GE</sub> = 0	_	2.30	3.00	V	
Reverse recove	ry time	t <sub>rr</sub>	I <sub>F</sub> = 100A, V <sub>GE</sub> = -10V di / dt = 100A / µs	_	0.08	0.15	μs	
Thermal resistance		R <sub>th (j-c)</sub>	Transistor stage	_	_	0.28	°C/W	
			Diode stage	_	_	0.69	] 0///	

Note 1: Switching time test circuit & timing chert



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